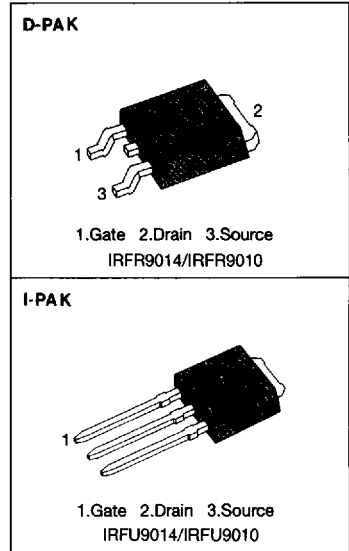


FEATURES

- Lower $R_{DS(ON)}$
- Improved inductive ruggedness
- Fast switching times
- Rugged polysilicon gate cell structure
- Lower input capacitance
- Extended safe operating area
- Improved high temperature reliability

PRODUCT SUMMARY

Part Number	Vds	RDS(on)	Id
IRFR9014/U9014	-60V	0.50 Ω	-5.3A
IRFR9010/U9010	-50V	0.50 Ω	-5.3A



ABSOLUTE MAXIMUM RATINGS

Characteristic	Symbol	IRFR9014/U9014	IRFR9010/U9010	Unit
Drain-Source Voltage (1)	V _{DSS}	-60	-50	V _{dc}
Drain-Gate Voltage (R _{Gs} =1.0M Ω)(1)	V _{DGR}	-60	-50	V _{dc}
Gate-Source Voltage	V _{GS}	± 20		V _{dc}
Continuous Drain Current T _c =25 °C	I _D	-5.3		A _{dc}
Continuous Drain Current T _c =100 °C	I _D	-3.3		A _{dc}
Drain Current - Pulsed (3)	I _{DM}	-21		A _{dc}
Gate Current - Pulsed	I _{GM}	± 1.5		A _{dc}
Single Pulsed Avalanche Energy (4)	E _{AS}	240		mJ
Avalanche Current	I _{AS}	-5.3		A
Total Power Dissipation at T _c =25 °C	P _D	25		Watts
Derate above 25 °C		0.20		W/ °C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150		°C
Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5 seconds	T _L	300		°C

Notes : (1) T_J=25°C to 150°C

(2) Pulse test : Pulse width $\leq 300\mu s$, Duty Cycle $\leq 2\%$

(3) Repetitive rating : Pulse width limited by max. junction temperature

(4) L=9.7mH, V_{dd}=-25V, R_G=25 Ω , Starting T_J=25°C

ELECTRICAL CHARACTERISTICS (Tc=25°C unless otherwise specified)

Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
BV _{DSS}	Drain-Source Breakdown Voltage					
	IRFR9014/IRFU9014	-60	-	-	V	V _{GS} =0V, I _D =-250μA
	IRFR9010/IRFU9010	-50	-	-	V	
V _{GS(th)}	Gate Threshold Voltage	-2.0	-	-4.0	V	V _{DS} =V _{GS} , I _D =-250μA
I _{GSS}	Gate-Source Leakage Forward	-	-	-100	nA	V _{GS} =-20V
I _{GSS}	Gate-Source Leakage Reverse	-	-	100	nA	V _{GS} =20V
I _{SS}	Zero Gate Voltage Drain Current	-	-	-250	μA	V _{DS} =-Max. Rating, V _{GS} =0V
		-	-	-1000	μA	V _{DS} =-0.8 Max. Rating, V _{GS} =0V, Tc=125°C
R _{DS(on)}	Static Drain-Source On-State Resistance (2)	-	-	0.50	Ω	V _{GS} =-10V, I _D =-2.7A
g _{fs}	Forward Transconductance (2)	1.1	-	-	∅	V _{DS} ≥-50V, I _D =-2.7A
C _{iss}	Input Capacitance	-	308	-	pF	V _{DS} =0V
C _{oss}	Output Capacitance	-	123	-	pF	V _{DS} =-25V
C _{rss}	Reverse Transfer Capacitance	-	55	-	pF	f=1.0MHz
t _{d(on)}	Turn-On Delay Time	-	-	9.2	ns	V _{DS} =-0.5BV _{DSS} , I _D =-5.3A, Z _θ =24 Ω (MOSFET switching times are essentially independent of operating temperature)
t _r	Rise Time	-	-	71	ns	
t _{d(off)}	Turn-Off Delay Time	-	-	20	ns	
t _f	Fall Time	-	-	59	ns	
Q _g	Total Gate Charge (Gate-Source Plus Gate-Drain)	-	-	17.5	nC	
Q _{gs}	Gate-Source Charge	-	4.6	-	nC	V _{GS} =-10V, I _D =-5.3A, V _{DS} =0.8 Max. Rating (Gate charge is essentially independent of operating temperature)
Q _{gd}	Gate-Drain ("Miller") Charge	-	6.1	-	nC	

THERMAL RESISTANCE

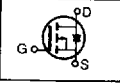
Symbol	Characteristics		All	Units	Remark
R _{thJC}	Junction-to-Case	MAX	5.0	K/W	
R _{thCS}	Case-to-Sink	TYP	1.7	K/W	Mounting surface flat, smooth and greased
R _{thJA}	Junction-to-Ambient	MAX	110	K/W	Free Air Operation

Notes : (1) T_J=25°C to 150°C

(2) Pulse test : Pulse width ≤ 300μs, Duty Cycle ≤ 2%

(3) Repetitive rating : Pulse width limited by max. junction temperature

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	-	-	-5.3	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier 
I_{SM}	Pulse Source Current (Body Diode) (3)	-	-	-21	A	
V_{SD}	Diode Forward Voltage	-	-	-5.5	V	$T_J=25^\circ\text{C}$, $I_S=-5.3\text{A}$, $V_{GS}=0\text{V}$
t_{rr}	Reverse Recovery Time	-	-	160	ns	$T_J=25^\circ\text{C}$, $I_F=-5.3\text{A}$, $dI_F/dt=100\text{A}/\mu\text{S}$

- Notes : (1) $T_J=25^\circ\text{C}$ to 150°C
 (2) Pulse test : Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
 (3) Repetitive rating : Pulse width limited by max. junction temperature

